- Short-Circuit Protection
- Offset-Voltage Null Capability
- Large Common-Mode and Differential Voltage Ranges
- No Frequency Compensation Required
- Low Power Consumption
- No Latch-Up
- Designed to Be Interchangeable With Fairchild uA741

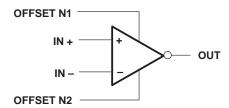
description

The μ A741 is a general-purpose operational amplifier featuring offset-voltage null capability.

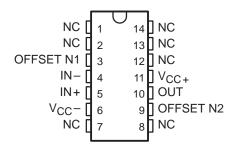
The high common-mode input voltage range and the absence of latch-up make the amplifier ideal for voltage-follower applications. The device is short-circuit protected and the internal frequency compensation ensures stability without external components. A low value potentiometer may be connected between the offset null inputs to null out the offset voltage as shown in Figure 2.

The μ A741C is characterized for operation from 0°C to 70°C. The μ A741I is characterized for operation from -40°C to 85°C.The μ A741M is characterized for operation over the full military temperature range of -55°C to 125°C.

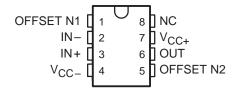
symbol



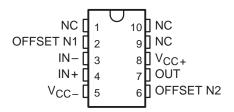
μΑ741M . . . J PACKAGE (TOP VIEW)



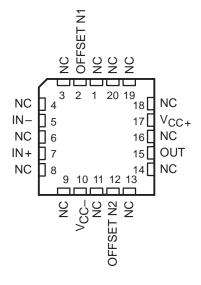
 $\mu\text{A741M}\dots\text{JG PACKAGE}$ $\mu\text{A741C}, \mu\text{A741I}\dots\text{D, P, OR PW PACKAGE}$ (TOP VIEW)



 $\begin{array}{c} \mu \text{A741M} \dots \text{U PACKAGE} \\ \text{(TOP VIEW)} \end{array}$



μΑ741M . . . FK PACKAGE (TOP VIEW)



NC - No internal connection

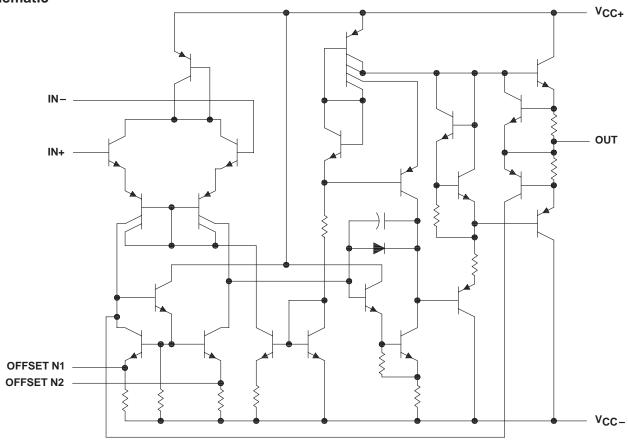


AVAILABLE OPTIONS

	PACKAGED DEVICES							
TA	SMALL OUTLINE (D)	CHIP CARRIER (FK)	CERAMIC DIP (J)	CERAMIC DIP (JG)	PLASTIC DIP (P)	TSSOP (PW)	FLAT PACK (U)	CHIP FORM (Y)
0°C to 70°C	μΑ741CD				μΑ741CP	μΑ741CPW		μΑ741Υ
-40°C to 85°C	μΑ741ID				μΑ741IP			
−55°C to 125°C		μΑ741MFK	μA741MJ	μΑ741MJG			μA741MU	

The D package is available taped and reeled. Add the suffix R (e.g., μ A741CDR).

schematic

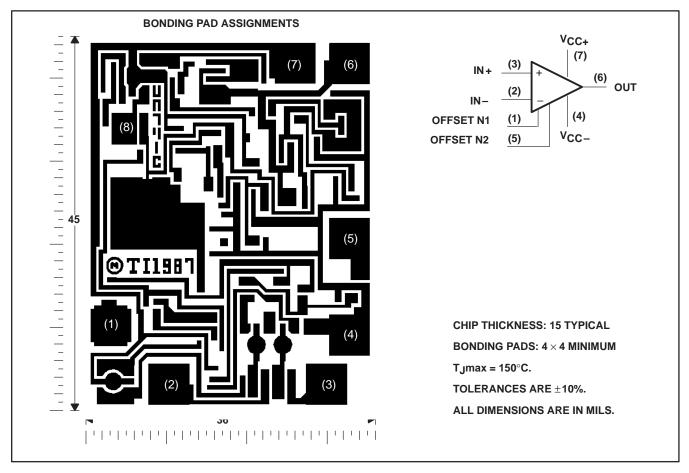


Component C	ount
Transistors	22
Resistors	11
Diode	1
Capacitor	1



μΑ741Y chip information

This chip, when properly assembled, displays characteristics similar to the μ A741C. Thermal compression or ultrasonic bonding may be used on the doped-aluminum bonding pads. Chips may be mounted with conductive epoxy or a gold-silicon preform.



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

			μ Α741 Ι	μ Α741Μ	UNIT	
Supply voltage, V _{CC+} (see Note 1)		18	22	22	V	
Supply voltage, V _{CC} (see Note 1)			-22	-22	V	
Differential input voltage, V _{ID} (see Note 2)			±30	±30	V	
Input voltage, V _I any input (see Notes 1 and 3)			±15	±15	V	
Voltage between offset null (either OFFSET N1 or OFFSET N2) and V _{CC} -			±0.5	±0.5	V	
Duration of output short circuit (see Note 4)			unlimited	unlimited		
Continuous total power dissipation		See Dissipation Rating Table				
Operating free-air temperature range, TA		0 to 70	-40 to 85	-55 to 125	°C	
Storage temperature range		-65 to 150	-65 to 150	-65 to 150	°C	
Case temperature for 60 seconds FK package				260	°C	
Lead temperature 1,6 mm (1/16 inch) from case for 60 seconds	J, JG, or U package			300	°C	
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds	D, P, or PW package	260	260		°C	

[†] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. All voltage values, unless otherwise noted, are with respect to the midpoint between VCC+ and VCC-.
 - 2. Differential voltages are at IN+ with respect to IN-.
 - 3. The magnitude of the input voltage must never exceed the magnitude of the supply voltage or 15 V, whichever is less.
 - 4. The output may be shorted to ground or either power supply. For the μA741M only, the unlimited duration of the short circuit applies at (or below) 125°C case temperature or 75°C free-air temperature.

DISSIPATION RATING TABLE

PACKAGE	T _A ≤ 25°C POWER RATING	DERATING FACTOR	DERATE ABOVE T _A	T _A = 70°C POWER RATING	T _A = 85°C POWER RATING	T _A = 125°C POWER RATING
D	500 mW	5.8 mW/°C	64°C	464 mW	377 mW	N/A
FK	500 mW	11.0 mW/°C	105°C	500 mW	500 mW	275 mW
J	500 mW	11.0 mW/°C	105°C	500 mW	500 mW	275 mW
JG	500 mW	8.4 mW/°C	90°C	500 mW	500 mW	210 mW
Р	500 mW	N/A	N/A	500 mW	500 mW	N/A
PW	525 mW	4.2 mW/°C	25°C	336 mW	N/A	N/A
U	500 mW	5.4 mW/°C	57°C	432 mW	351 mW	135 mW



electrical characteristics at specified free-air temperature, $V_{\text{CC}\pm}$ = ± 15 V (unless otherwise noted)

PARAMETER		TEST	- +	ŀ	ι Α741C		μ Α74	UNIT			
	PARAMETER	CONDITIONS	T _A †	MIN	TYP	MAX	MIN	TYP	MAX	UNII	
VIO	Input offset voltage	V _O = 0	25°C		1	6		1	5	mV	
٧١٥	input onset voltage	VO = 0	Full range			7.5			6	111 V	
ΔV IO(adj)	Offset voltage adjust range	VO = 0	25°C		±15			±15		mV	
lio	Input offset current	V _O = 0	25°C		20	200		20	200	nA	
liO	,	10-0	Full range			300			500	ПА	
l _{IB}	Input bias current	V _O = 0	25°C		80	500		80	500	nA	
цВ	input bias current	VO = 0	Full range			800			1500	ш	
VICR	Common-mode input		25°C	±12	±13		±12	±13		V	
VICR	voltage range		Full range	±12			±12				
	Maximum peak output voltage swing	$R_L = 10 \text{ k}\Omega$	25°C	±12	±14		±12	±14		V	
VOM		$R_L \ge 10 \text{ k}\Omega$	Full range	±12			±12				
VOM		$R_L = 2 k\Omega$	25°C	±10	±13		±10	±13			
		$R_L \ge 2 k\Omega$	Full range	±10			±10				
Δ, τρ	Large-signal differential voltage amplification $R_L ≥ 2 kΩ$ $V_O = ±10 V$	$R_L \ge 2 k\Omega$	25°C	20	200		50	200		V/mV	
AVD		V _O = ±10 V	Full range	15			25			V/IIIV	
rį	Input resistance		25°C	0.3	2		0.3	2		МΩ	
r _O	Output resistance	$V_O = 0$, See Note 5	25°C		75			75		Ω	
Ci	Input capacitance		25°C		1.4			1.4		pF	
CMRR	Common-mode rejection	Common-mode rejection	V _{IC} = V _{ICR} min	25°C	70	90		70	90		dB
CIVIKK	ratio	AIC = AICKIIIIII	Full range	70			70			dБ	
kovo	Supply voltage sensitivity	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	25°C		30	150		30	150	μV/V	
ksvs	$(\nabla \Lambda^{IO}/\nabla \Lambda^{CC})$	$V_{CC} = \pm 9 \text{ V to } \pm 15 \text{ V}$	Full range			150			150		
los	Short-circuit output current		25°C		±25	±40		±25	±40	mA	
loc	Supply current	$V_{O} = 0$, No load	25°C		1.7	2.8		1.7	2.8	mA	
ICC		VO = 0, No load	Full range			3.3			3.3	ША	
PD	Total power dissipation	$V_{\Omega} = 0$, No load	25°C		50	85		50	85	mW	
ט ין	Total power dissipation	Full ra	Full range			100			100	11177	

[†] All characteristics are measured under open-loop conditions with zero common-mode input voltage unless otherwise specified. Full range for the μ A741C is 0°C to 70°C, the μ A741I is -40°C to 85°C, and the μ A741M is -55°C to 125°C.

operating characteristics, $V_{CC\pm}$ = ± 15 V, T_A = $25^{\circ}C$

PARAMETER		TEST CONDITIONS		μ Α741C			μ Α741Ι, μ Α741Μ			UNIT
				MIN	TYP	MAX	MIN	TYP	MAX	UNIT
t _r	Rise time	$V_{\parallel} = 20 \text{ mV}, \qquad R_{\perp} = 2 \text{ k}\Omega,$			0.3			0.3		μs
	Overshoot factor	$C_L = 100 pF$,	See Figure 1		5%			5%		
SR	Slew rate at unity gain	V _I = 10 V, C _L = 100 pF,	$R_L = 2 kΩ$, See Figure 1		0.5			0.5		V/μs

NOTE 5: This typical value applies only at frequencies above a few hundred hertz because of the effects of drift and thermal feedback.

electrical characteristics at specified free-air temperature, $V_{CC\pm}$ = ± 15 V, T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	ļ	ι Α741Υ		LINIT	
	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
VIO	Input offset voltage	V _O = 0		1	6	mV	
$\Delta V_{IO(adj)}$	Offset voltage adjust range	V _O = 0		±15		mV	
I _{IO}	Input offset current	V _O = 0		20	200	nA	
I_{IB}	Input bias current	V _O = 0		80	500	nA	
VICR	Common-mode input voltage range		±12	±13		V	
Van	Maximum peak output voltage swing	$R_L = 10 \text{ k}\Omega$	±12	±14		V	
VOM	Maximum peak output voltage swing	$R_L = 2 k\Omega$	±10	±13		v	
A_{VD}	Large-signal differential voltage amplification	$R_L \ge 2 k\Omega$	20	200		V/mV	
rį	Input resistance		0.3	2		МΩ	
r _o	Output resistance	$V_O = 0$, See Note 5		75		Ω	
Ci	Input capacitance			1.4		pF	
CMRR	Common-mode rejection ratio	V _{IC} = V _{ICR} min	70	90		dB	
ksvs	Supply voltage sensitivity ($\Delta V_{IO}/\Delta V_{CC}$)	$V_{CC} = \pm 9 \text{ V to } \pm 15 \text{ V}$		30	150	μV/V	
los	Short-circuit output current			±25	±40	mA	
Icc	Supply current	$V_O = 0$, No load		1.7	2.8	mA	
PD	Total power dissipation	V _O = 0, No load		50	85	mW	

[†] All characteristics are measured under open-loop conditions with zero common-mode voltage unless otherwise specified.

NOTE 5: This typical value applies only at frequencies above a few hundred hertz because of the effects of drift and thermal feedback.

operating characteristics, $V_{CC}\pm$ = ±15 V, T_A = 25°C

PARAMETER		TEST CONDITIONS	μ Α741Υ			UNIT
		TEST CONDITIONS	MIN	TYP	MAX	UNIT
t _r	Rise time	$V_{\parallel} = 20 \text{ mV}, R_{\perp} = 2 \text{ k}\Omega,$		0.3		μs
		C _L = 100 pF, See Figure 1		5%		
SR	Slew rate at unity gain	V_{I} = 10 V, R_{L} = 2 k Ω , C_{L} = 100 pF, See Figure 1		0.5		V/μs



PARAMETER MEASUREMENT INFORMATION

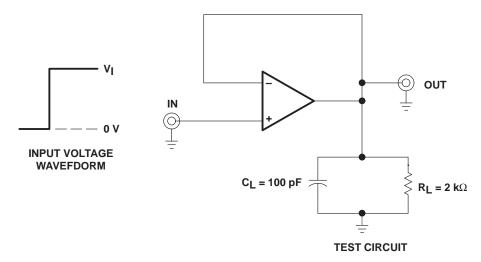


Figure 1. Rise Time, Overshoot, and Slew Rate

APPLICATION INFORMATION

Figure 2 shows a diagram for an input offset voltage null circuit.

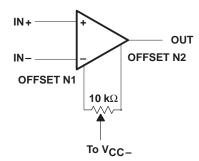
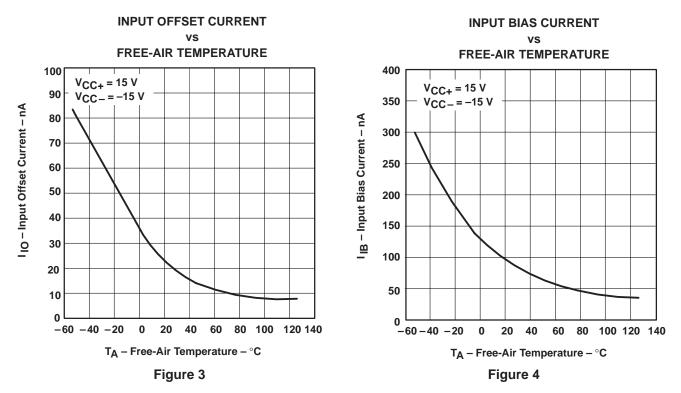
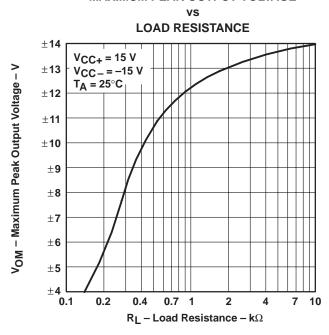


Figure 2. Input Offset Voltage Null Circuit

TYPICAL CHARACTERISTICS[†]



MAXIMUM PEAK OUTPUT VOLTAGE

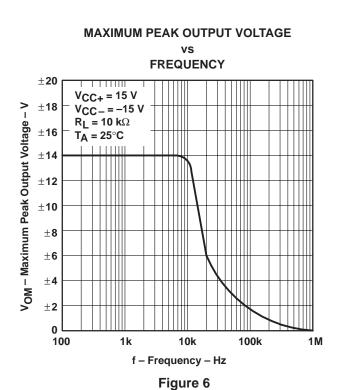


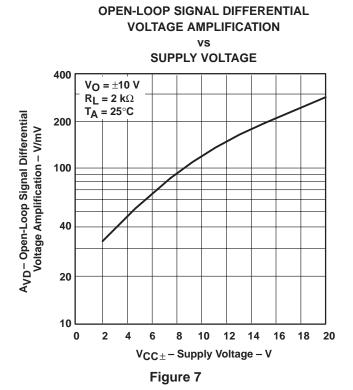
[†] Data at high and low temperatures are applicable only within the rated operating free-air temperature ranges of the various devices.



Figure 5

TYPICAL CHARACTERISTICS



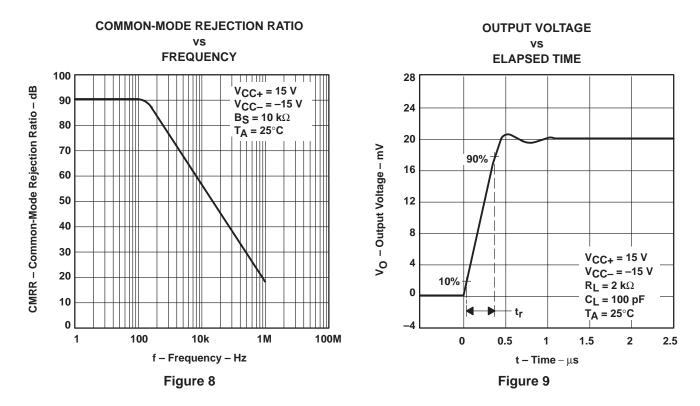


OPEN-LOOP LARGE-SIGNAL DIFFERENTIAL VOLTAGE AMPLIFICATION

vs **FREQUENCY** 110 $V_{CC+} = 15 V$ 100 V_{CC}_ = -15 V 90 A_{VD} - Open-Loop Signal Differential $V_0 = \pm 10 \text{ V}$ $R_1 = 2 k\Omega$ 80 Voltage Amplification - dB TA = 25°C 70 60 50 40 30 20 10 0 -10 100 10k 100k 1M 10 1k 10M f - Frequency - Hz



TYPICAL CHARACTERISTICS



VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE

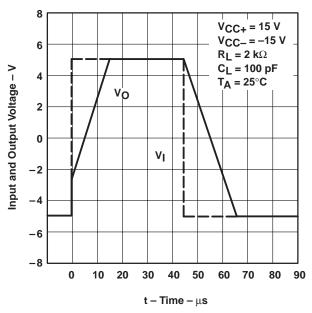


Figure 10



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